

Customer No.: 31561
Docket No.: 13531-US-PA
Application No.: 10/711,498

To the Claims:

Claims 1-7 (cancelled)

8. (original) A pixel structure for a liquid crystal display panel, comprising:

a first substrate;

a single-type low temperature polysilicon thin film transistor disposed over the first substrate;

a pixel structure disposed over the first substrate and electrically connected to the single-type low temperature polysilicon thin film transistor;

a storage capacitor disposed over the first substrate, wherein one of the terminals of the storage capacitor is electrically connected to the single-type low temperature polysilicon thin film transistor and the storage capacitor is regarded as a symmetrical capacitor related to the single-type low temperature polysilicon thin film transistor;

a second substrate disposed over the first substrate;

an electrode film disposed on the second substrate;

a liquid crystal layer disposed between the first substrate and the second substrate; and

a liquid crystal capacitor disposed between the first substrate and the second substrate,

wherein one of the terminals of the liquid crystal capacitor is electrically connected to the single-type low temperature polysilicon thin film transistor while the other terminal of the liquid crystal capacitor and the other terminal of the storage capacitor are electrically connected to a common electrode.

9. (original) The pixel structure of claim 8, wherein the single-type low temperature polysilicon thin film transistor comprises a P-type low temperature polysilicon thin film transistor.

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10. (original) The pixel structure of claim 9, wherein the terminals of the storage capacitor comprises a top electrode and a bottom electrode such that the bottom electrode is a P-doped region.

11. (original) The pixel structure of claim 8, wherein the single-type low temperature polysilicon thin film transistor comprises an N-type low temperature polysilicon thin film transistor.

12. (original) The pixel structure of claim 11, wherein the terminals of the storage capacitor comprises a top electrode and a bottom electrode such that the bottom electrode is an N-doped region.

13. (original) The pixel structure of claim 8, wherein the single-type low temperature polysilicon thin film transistor comprises a single gate low temperature polysilicon thin film transistor or a dual gate low temperature polysilicon thin film transistor.

14. (original) The pixel structure of claim 8, wherein the terminals of the liquid crystal capacitor comprises the electrode film and the pixel electrode.

15. (original) The pixel structure of claim 8, further comprising a color filter layer disposed between the second substrate and the electrode film.

16. (cancelled)